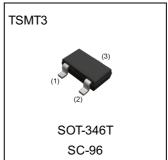


#### PNP -2.5A -80V Middle Power Transistor

Parameter	Value
$V_{CEO}$	-80V
IC	-2.5A

#### Outline

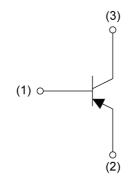


#### Features

- 1)Suitable for Middle Power Driver
- 2)Complementary PNP Types:2SCR544R
- 3)Low V<sub>CE(sat)</sub>

 $V_{CE(sat)}$ =-400mV (Max.) ( $I_C/I_B$ =-1A/-50mA)

#### •Inner circuit



- (1) Base
- (2) Emitter
- (3) Collector

### Application

LOW FREQUENCY AMPLIFIER, HIGH SPEED SWITCHING

# Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SAR544R	TSMT3	2928	TL	180	8	3000	MS

# ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter	Symbol	Values	Unit	
Collector-base voltage	$V_{CBO}$	-80	V	
Collector-emitter voltage	V <sub>CEO</sub> -80			
Emitter-base voltage	$V_{EBO}$	-6	V	
Collector current	I <sub>C</sub>	-2.5	Α	
Collector current	I <sub>CP</sub> *1	-5	Α	
Dever discipation	P <sub>D</sub> *2	0.5	W	
Power dissipation	P <sub>D</sub> *3	1.0	W	
Junction temperature	T <sub>j</sub>	150	°C	
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C	

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

Doromotor	Cumbal	Conditions	Values			Lloit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = -100μA	-80	-	-	V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = -1mA	-80	-	-	V
Emitter-base breakdown voltage	$BV_{EBO}$	I <sub>E</sub> = -100μA	-6	-	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -80V	1	-	-1.0	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V	-	-	-1.0	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -1A, I <sub>B</sub> = -50mA	-	-200	-400	mV
DC current gain	h <sub>FE</sub>	$V_{CE} = -3V, I_{C} = -100 \text{mA}$	120	-	390	-
Transition frequency	f <sub>T</sub>	$V_{CE} = -10V, I_{E} = 500 \text{mA},$ f = 100MHz	-	280	-	MHz
Output capacitance	C <sub>ob</sub>	$V_{CB} = -10V$ , $I_E = 0mA$ , $f = 1MHz$	-	32	-	pF
Turn-On time	t <sub>on</sub>	I <sub>C</sub> = -1.3A, I <sub>B1</sub> = -130mA,	-	50	-	ns
Storage time	t <sub>stg</sub>	$I_{B2} = 130 \text{mA},$ $V_{CC} \simeq -10 \text{V},$	-	400	-	ns
Fall time	t <sub>f</sub>	$R_L = 7.5\Omega$ See test circuit	-	40	-	ns

<sup>\*1</sup> Pw=10ms, Single pulse

<sup>\*2</sup> Each terminal mounted on a reference land.

<sup>\*3</sup> Mounted on a ceramic board(40×40×0.7mm).

### ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

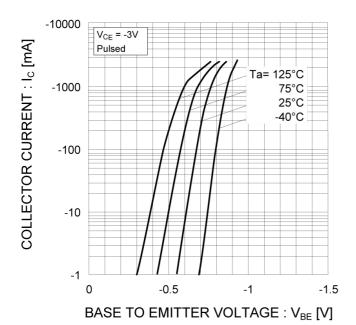
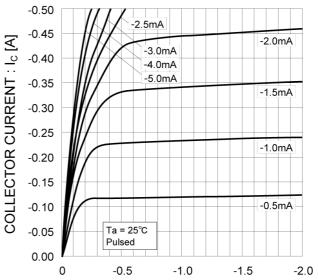


Fig.2 Typical Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: V<sub>CE</sub> [V]

Fig.3 DC Current Gain vs. Collector Current (I)

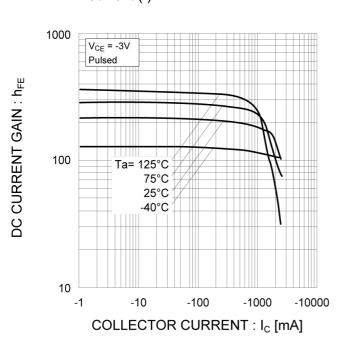
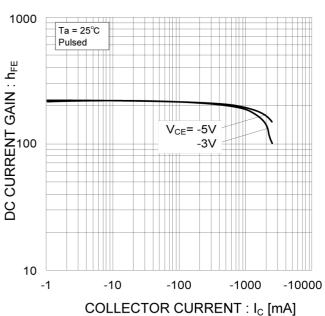


Fig.4 DC Current Gain vs. Collector Current (II)



# ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

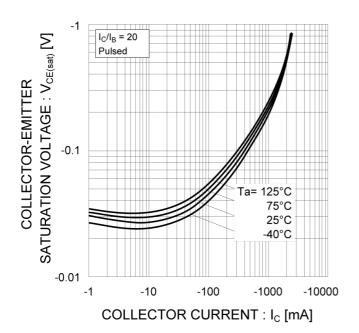


Fig.6 Collector-Emitter Saturation
Voltage vs. Collector Current (II)

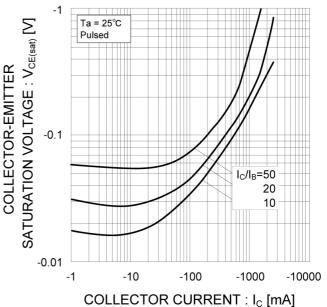


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

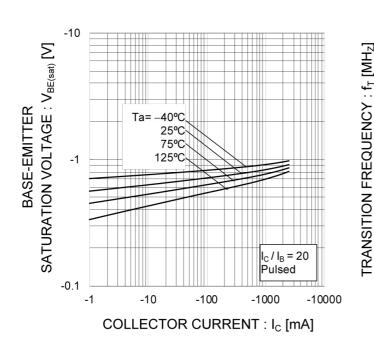
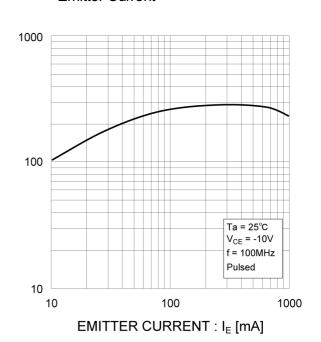


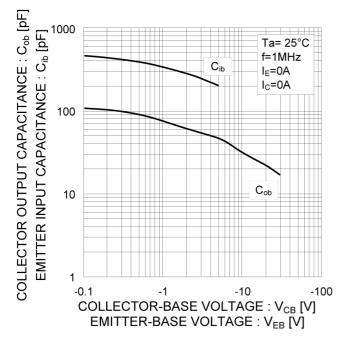
Fig.8 Gain Bandwidth Product vs. Emitter Current

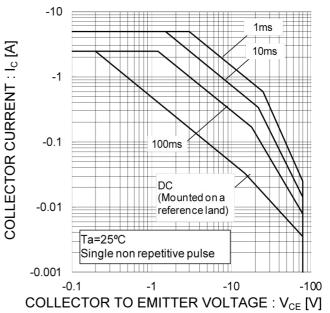


# ● Electrical characteristic curves(T<sub>a</sub> = 25°C)

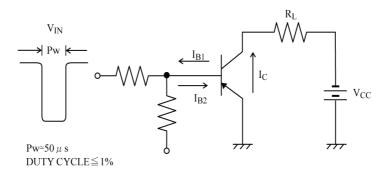
Fig.9 Emitter Input Capacitance vs.
Emitter-Base Voltage
Collector Output Capacitance vs.
Collector-Base Voltage

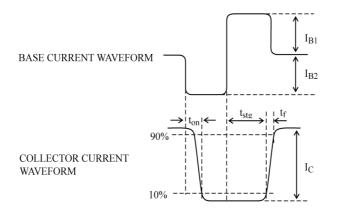
Fig.10 Safe Operating Area





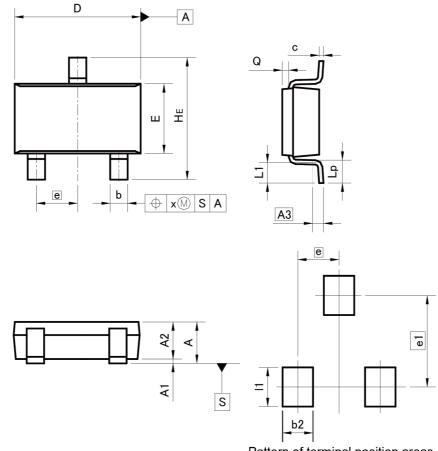
#### SWITCHING TIME TEST CIRCUIT





#### Dimensions

TSMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES	
MIN		MAX	MIN	MAX	
Α	I	1.00	-	0.039	
A1	0.00	0.10	0.000	0.004	
A2	0.75	0.95	0.030	0.037	
A3	0.25		0.010		
b	0.35	0.50	0.014	0.020	
С	0.10	0.26	0.004	0.010	
D	2.80	3.00	0.110	0.118	
E	1.50	1.80	0.059	0.071	
е	0.9	95	0.0	37	
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.05	0.25	0.002	0.010	
Х	-	0.20	-	0.008	

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
b2		0.70	_	0.028	
e1	2.	10	0.0	83	
11	_	0.90	-	0.035	

Dimension in mm/inches



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